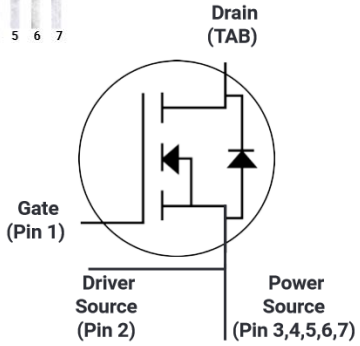
Silicon Carbide Power MOSFET （N-Channel Enhancement）

V_{DS}	1200V
$I_{D\ (25°C)}$	23A
$R_{DS(on)}$	120mΩ



Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package**: TO263-7L
- **Terminals**: Tin plated leads
- **Polarity**: As marked

■Maximum Ratings (T_C=25℃ Unless otherwise specified）

PARAMTETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code			D2120120B7GH		
Drain source voltage @ T_j=25°C	$V_{DS,max}$	V	1200	V_{GS}=0 V, I_D=100uA	
Gate source voltage @ T_j=25°C	$V_{GS,max}$	V	-10/+25	Absolute maximum values (AC f > 1Hz, duty cycle < 1%)	Note1
Gate source voltage @ T_j=25°C	$V_{GS,op}$	V	-5/+20	Recommended operational values	
Continuous drain current @ T_c=25°C	I_D	A	23	V_{GS}=20V, Tc=25℃	Fig.14
Continuous drain current @ T_c=110°C			16	V_{GS}=20V, Tc=110℃	
Pulse Drain Current	$I_{D,\ pulse}$	A	63	Limited by t_{pw}	Fig.15
Avalanche energy, Single Pulse	E_{AS}	mJ	200	V_{DD}=75V, L=25mH	
Power Dissipation	P_{TOT}	W	161	T_c=25°C , Tj = 175℃	Fig.13
Operating junction and Storage temperature range	Tj ,Tstg	°C	-55 to +175		
Soldering temperature	T_L	°C	260	1.6mm (0.063'') from case for 10s	

■Static Electrical Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	$V_{GS(th)}$	V	1.5	2.95	4.0	V_{DS}=V_{GS}, I_D= 10mA	Fig.4, 11
Drain source breakdown voltage	$V_{(BR)DSS}$	V	1200			V_{GS}=0, I_D=100uA	
Zero gate voltage drain current	I_{DSS}	uA		<1	50	V_{DS}=1200V, V_{GS}= 0V	
				10	500	V_{DS}=1200V, V_{GS}= 0V, Tj= 175℃	
Gate source leakage current	I_{GSS}	nA			250	V_{GS}= 20V, V_{DS}=0V	
Current drain source on-state resistance	$R_{DS\ ON}$	mΩ		120	160	V_{GS}=20V, I_D=10A	Fig.3, 5, 6
				200		V_{GS}=20V, I_D=10A,Tj=175℃	
Transconductance	g_f	S		4.5		V_{DS}=20V,I_D=10A	

■Dynamic Electrical Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	Ciss	pF		1083		V_{DS}=800V, V_{GS}=0V, Tj=25℃, f=1MHz, V_{AC}= 25mV	Fig.10
Output capacitance	Coss			56			
Reverse capacitance	Crss			8			
Coss stored energy	Eoss	uJ		23			Fig.12
Gate source charge	Qgs	nC		14.5		V_{DS}=800V, V_{GS}=-5/20V, I_D=10A	Fig.16
Gate drain charge	Qgd			29			
Gate charge	Qg			67			
Internal Gate Resistance	$R_{G(int)}$	Ω		2.5	5.0	f =1MHz, V_{AC}= 25mV	

■Switching Characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	$t_{d(on)}$	ns		6		V_{DD}=800V, V_{GS}=-5/+20V, I_D=10A, L=300uH, $R_{G(ext)}$= 2.7Ω	
Rise time	t_r			15			
Turn off delay time	$t_{d(off)}$			16			
Fall time	t_f			16			
Turn on switching energy	Eon	uJ		122			Fig.17, 18
Turn off switching energy	Eoff			41.4			

■Body diode characteristics（Tc=25℃ unless otherwise specified ）

PARAMTETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V_{SD}	V		3.4		V_{GS}=0V,I_{SD}=2.5A	Fig.8
Continuous diode forward current	I_S	A		25		V_{GS}=0V,Tc=25℃	
Reverse recovery time	trr	nS		53		V_{DS}=400V, V_{GS}=0V, I_{SD}=10A, di/dt=300A/uS	
Reverse recovery charge	Qrr	nC		63			
Peak reverse recovery current	Irrm	A		2.25			

Note 1: When using SiC Body Diode the maximun recommended V_{GS} = -5V

■Thermal Characteristics （T_a=25℃ Unless otherwise specified）

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	$R_{\theta J-C}$	°C /W	0.93

■Typical Characteristics

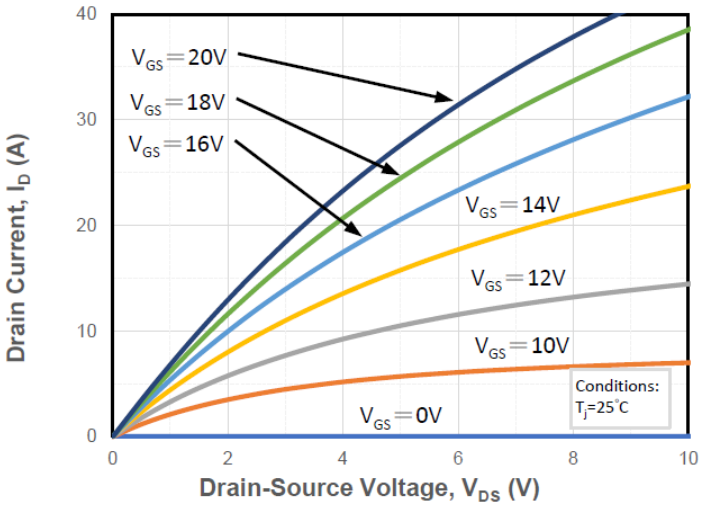


Figure 1. Output Characteristics Tj = 25℃

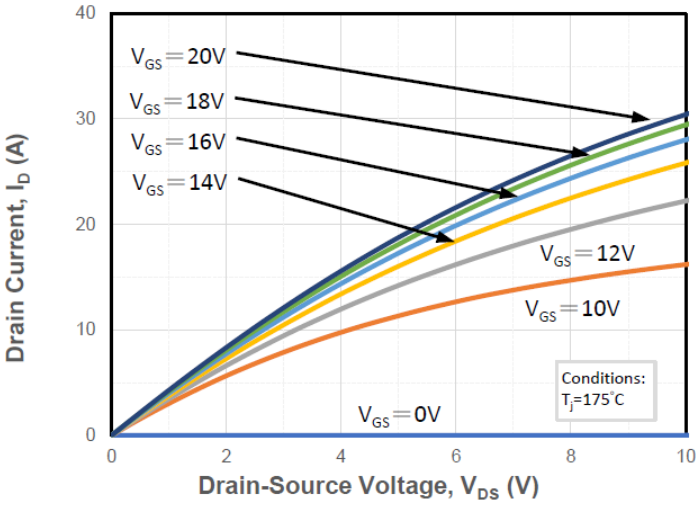


Figure2. Output Characteristics Tj = 175℃

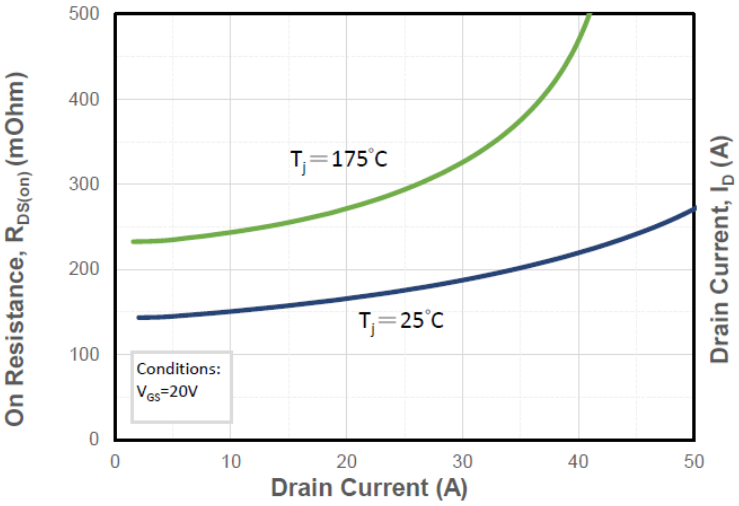


Figure 3. On-resistance vs. drain current

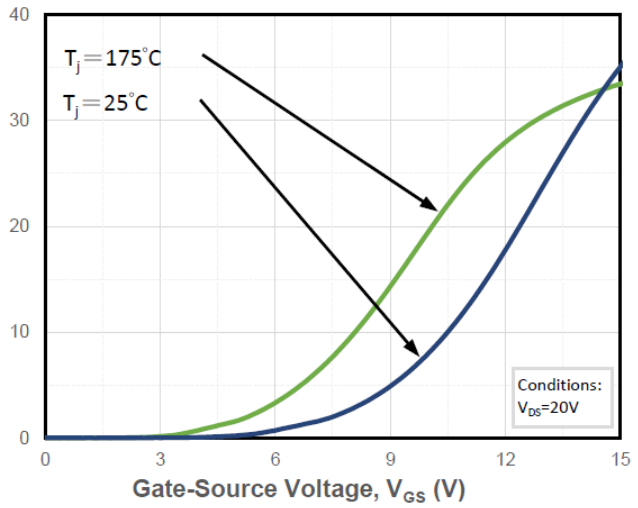


Figure 4. Transfer Characteristics for various Tj

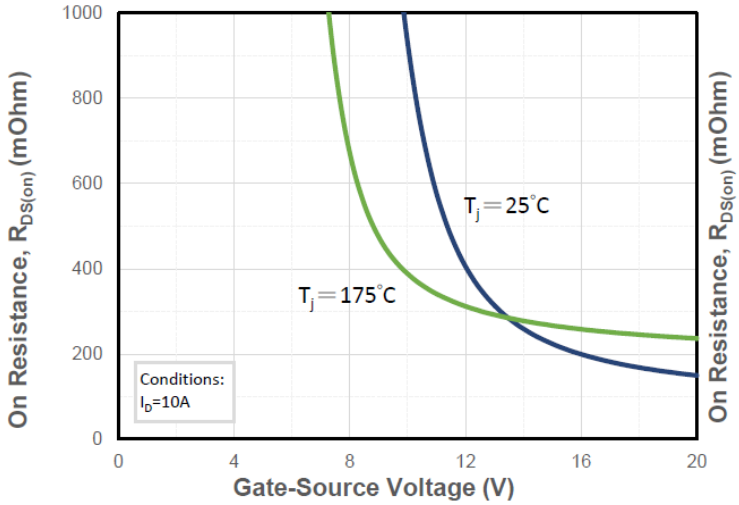


Figure 5. On-resistance vs. gate voltage for various Tj

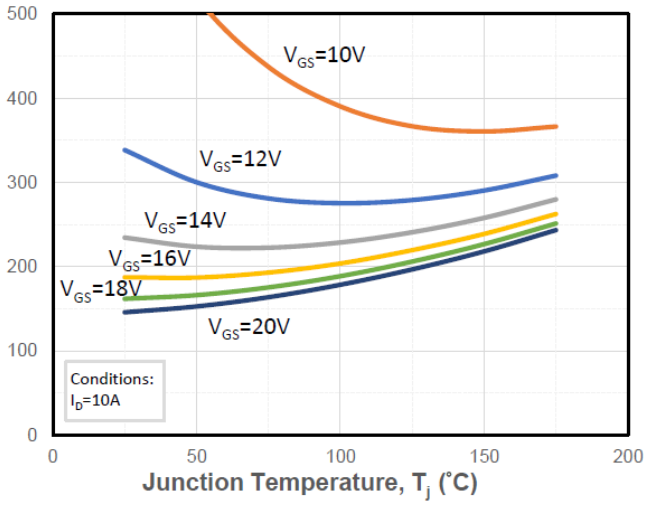


Figure 6. On-resistance vs. Temperature for various Gate voltage

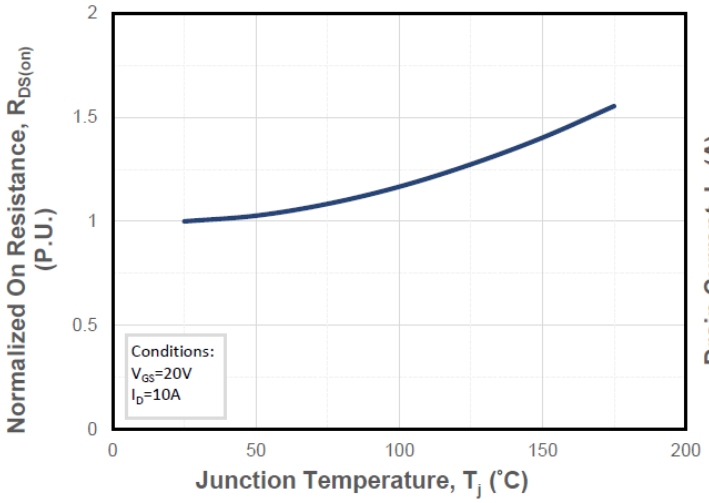


Figure 7. Normalized On-Resistance vs.Temperature

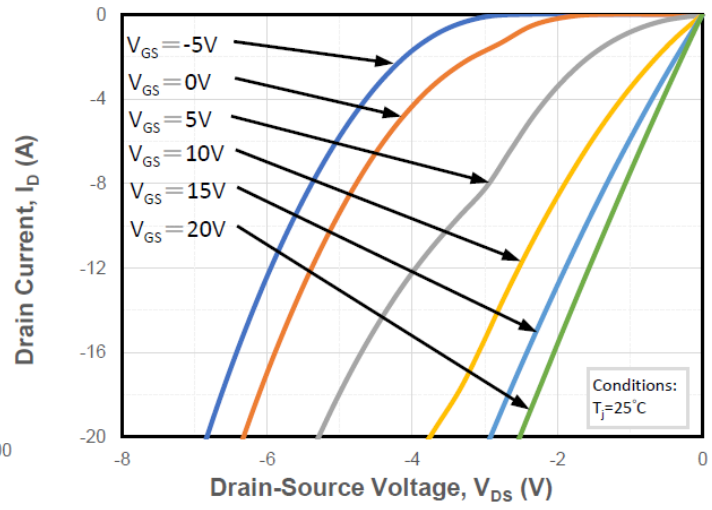


Figure 8. Reverse Output Characteristics at Tj = 25°C

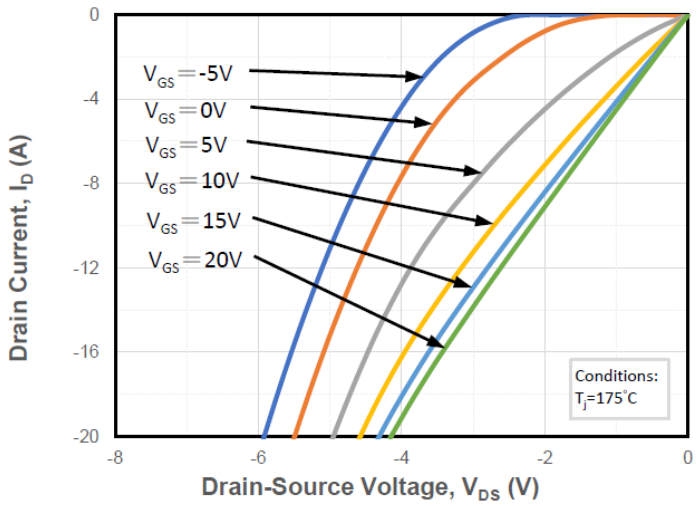


Figure 9. Reverse Output Characteristics at Tj = 175°C

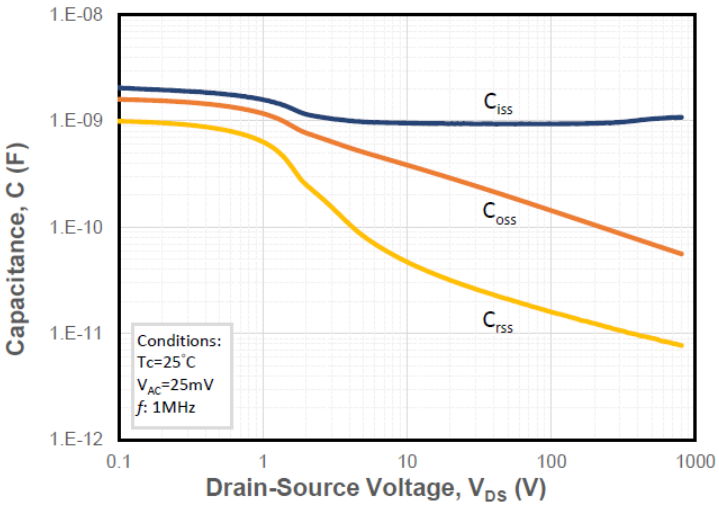


Figure 10. Capacitances vs. Drain to Source Voltage

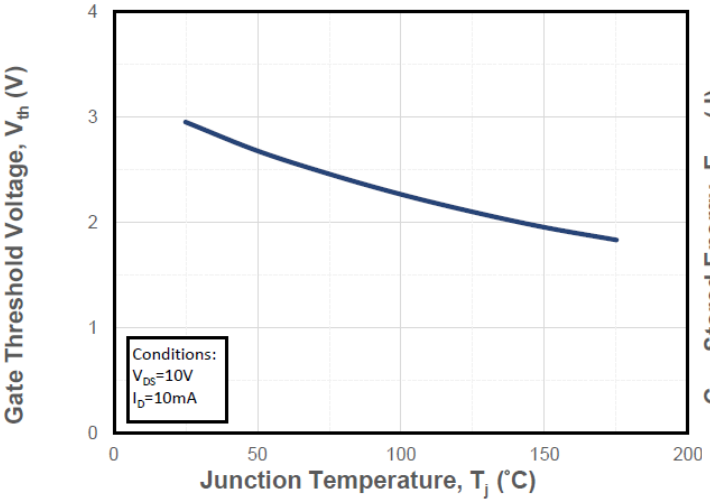


Figure 11. Threshold voltage vs.temperature

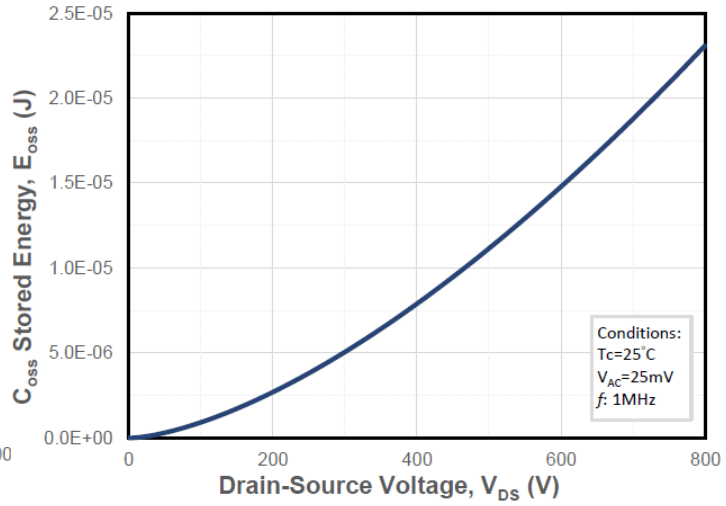


Figure 12. Output Capacitor Stored Energy

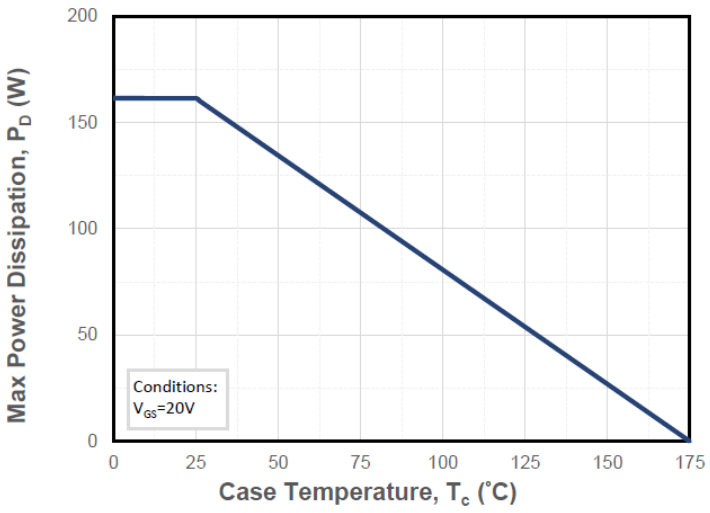


Figure 13. Maximum Power Dissipation Derating vs. Case Temperature

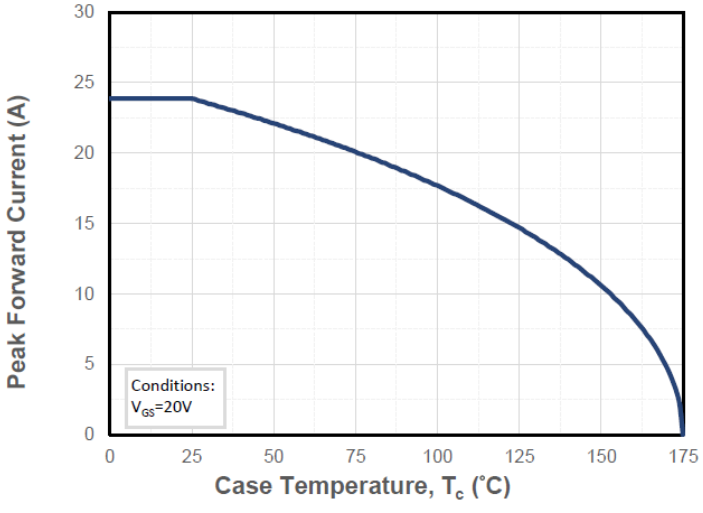


Figure 14. Drain Current Derating vs. Case Temperature

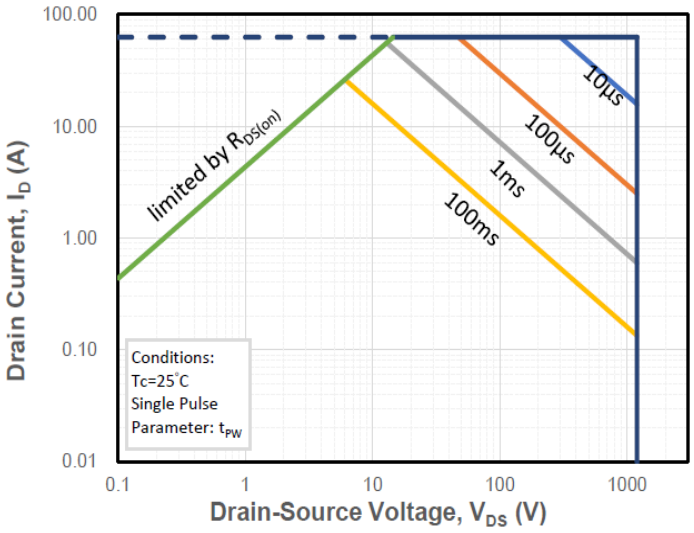


Figure 15. Safe Operating Area

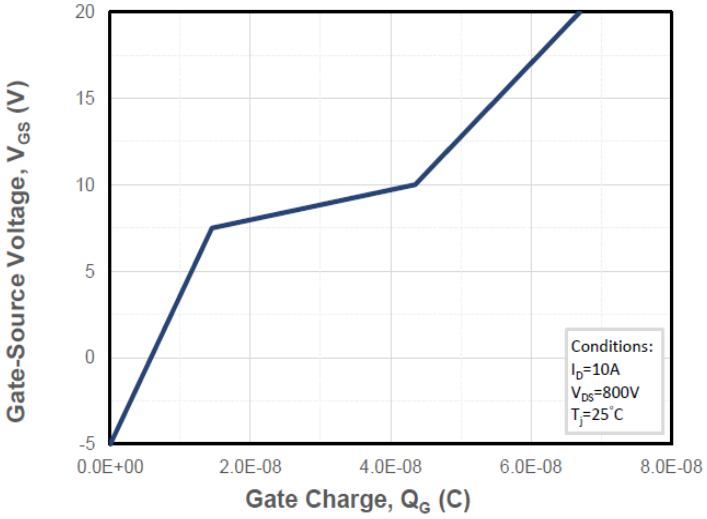


Figure 16. Gate Charge Characteristics

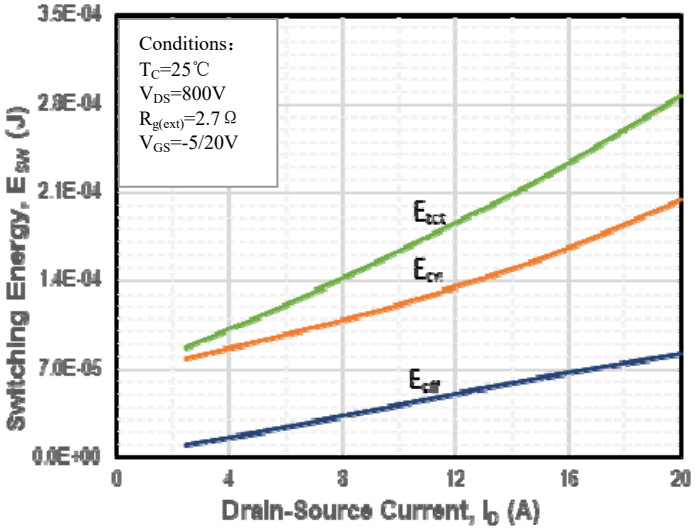


Figure 17. Clamped Inductive Switching Energy vs. Drain Current

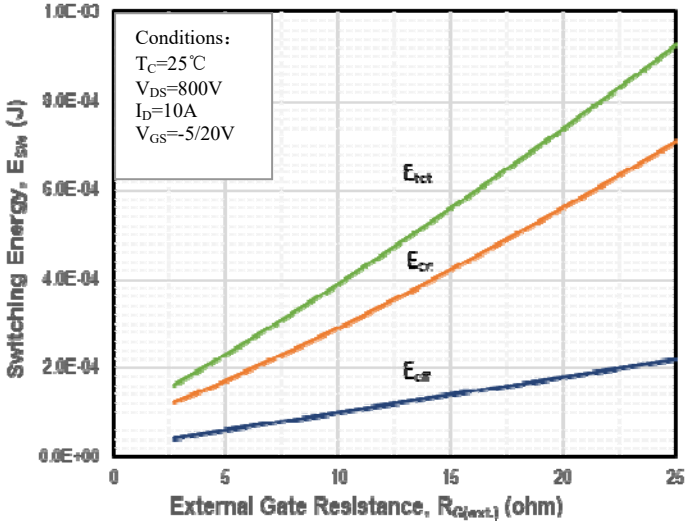


Figure 18. Clamped Inductive Switching Energy vs. External Gate Resistor (R_G(ext.))

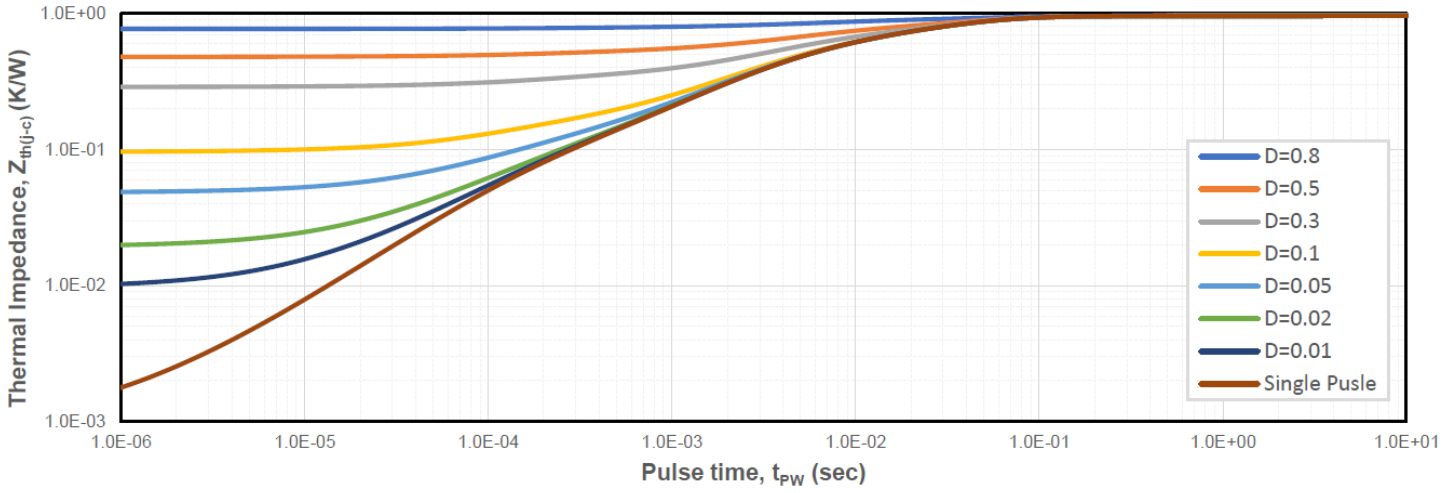


Figure 19. Transient Junction to Case Thermal Impedance

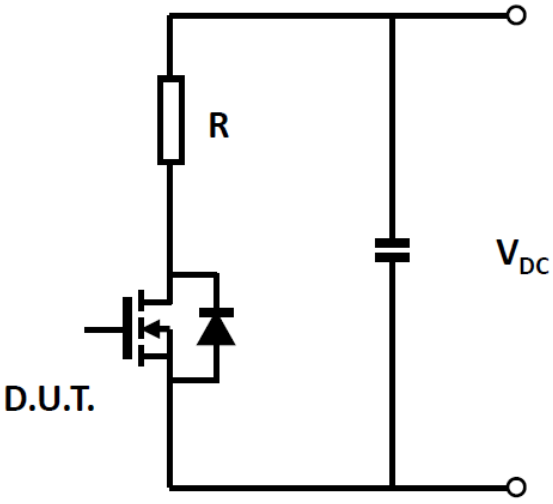


Figure 20. Schematic of Resistive Switching

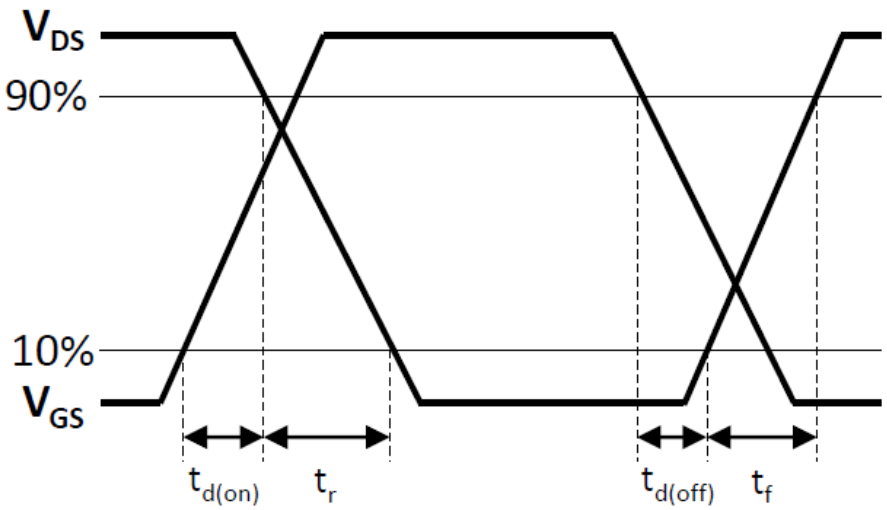
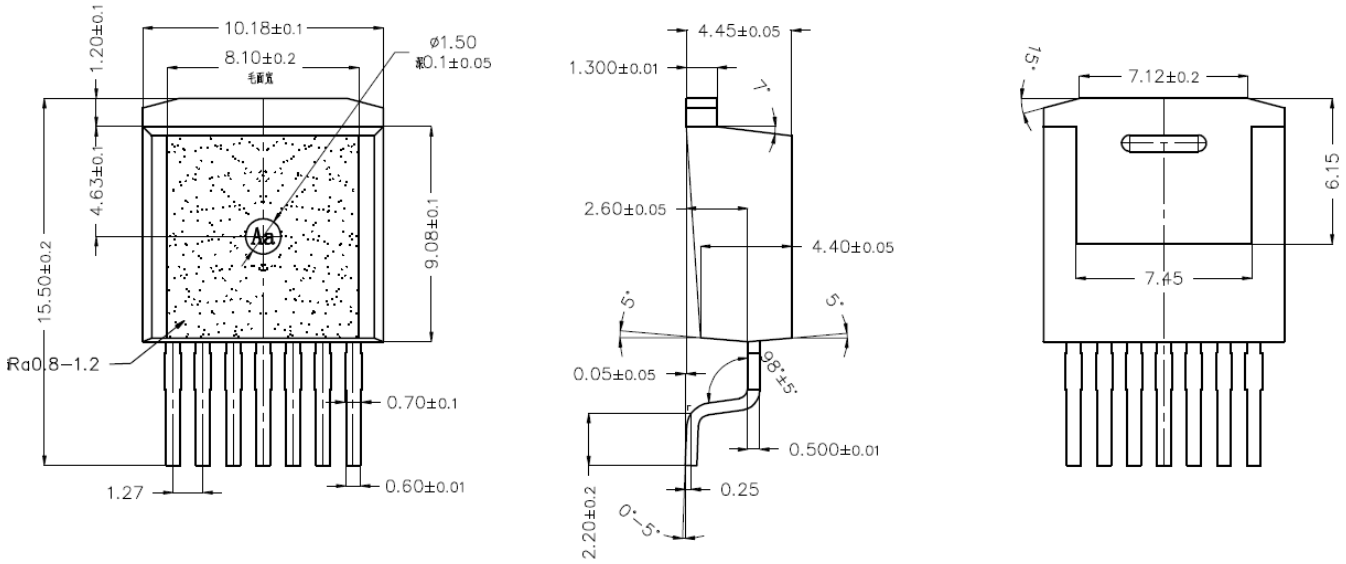


Figure 21. Switching Times Definition

■Outline Dimensions



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